

#### **POWER PIN DIODES**

#### **DESCRIPTION**

These series of PIN diodes are designed for applications requiring small package size and moderate average power handling capability. The low capacitance of the UM6000 and UM6600 allows them to be used as series switching elements to 1 GHz. The low resistance of the UM6200 is useful in applications where forward bias current must be minimized.

Because of its thick I-region width and long lifetime the UM6000 and UM6600 have been used in distortion sensitive and high peak power applications, including receiver protectors, TACN, and IFF equipment. Their low capacitance allows them to be useful as attenuator diodes at frequencies greater than 1 GHz. The UM6200 has been

used successfully in switches in which low insertion loss at low bias current is required. The "A" style package for this series is the smallest Microsemi PIN diode package. It has been used successfully in many microwave applications using coaxial, microstrip, and stripline techniques at frequencies beyond X-Band. The "B" and "E" style leaded packages offer the highest available power dissipation for a package this small. They have been used extensively as series switch elements in microstrip circuits. The "C" style package duplicates the physical outline available in conventional ceramic-metal packages but incorporates the many reliability advantages of the Microsemi construction.

#### **KEY FEATURES**

- Voltage ratings to 1000V
- Average power dissipation to 6 W
- Series resistance as low as 0.4  $\Omega$
- Carrier lifetime greater than 1.0 µs
- Non cavity design
- Thermally matched configuration
- Low capacitance at 0 V bias
- Low conductance at 0 V bias
- Compatible with automatic insertion equipment

IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

#### ABSOLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED) **Package** Condition UM6000/UM6600 **UM6200** PD PD θ 25 °C Pin Temperature 25 °C/W A & C 6 W 4 W 37.5 °C/W **B & E** ½ in. total length to 25 °C Contact 60 °C/W 2.0 W 75 °C/W 2.5 W 0.5 W 0.5 W 25 °C End Cap Temperature 27.5°C/W SM 4.5 W 3.0 W 42.5 °C/W UM6000 25 kW ΑII 1 us pulse (Single) 10 kW UM6600 13 kW

| VOLTAGE RATINGS         |        |        |        |  |  |  |
|-------------------------|--------|--------|--------|--|--|--|
| Reverse Voltage @ 10 uA |        |        |        |  |  |  |
| 100                     | UM6001 | UM6201 | UM6601 |  |  |  |
| 200                     | UM6002 | UM6202 | UM6602 |  |  |  |
| 400                     | -      | UM6204 | -      |  |  |  |
| 800                     | UM6006 | -      | UM6606 |  |  |  |
| 1000                    | UM6010 | -      | UM6610 |  |  |  |

### APPLICATIONS/BENEFITS

- Isolated stud package available
- Surface mount package available
- RoHS compliant packaging available: use UMX6001B, etc.

UM6000/UM62000/UM660



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| ELECTRICAL PARAMETERS @ 25°C (unless otherwise specified) |                |  |        |        |        |       |  |
|---|----------------|--|--------|--------|--------|-------|--|
| Parameter   | Symbol         | Conditions                                 | UM6600 | UM6000 | UM6200 | Units |  |
|   |                |  |        |        |        |       |  |
| Reverse Current (Max)                                     | I <sub>R</sub> | At rated voltage                           | 10     | 10     | 10     | uA    |  |
| Series Resistance(Max)                                    | Rs             | If = 100 mA, F= 100 MHz                    | 2.5    | 1.7    | 0.4    | Ohms  |  |
| Capacitance (Max)   | Ст             | $V_R = 100 \text{ V}, F = 1 \text{ MH}_Z$  | 0.4    | 0.5    | 1.1    | pF    |  |
| Parallel Resistance(Min)                                  | ) Rp           | $V_R = 100 \text{ V}, F = 100 \text{ MHz}$ | 300k   | 300k   | 350k   | Ohms  |  |
| Carrier Lifetime(Min)                                     | τ              | I <sub>F</sub> = 10 mA                     | 1.0    | 1.0    | 0.6    | us    |  |
| I-Region Width (Min)                                      | W              | -  | 150    | 150    | 40     | um    |  |

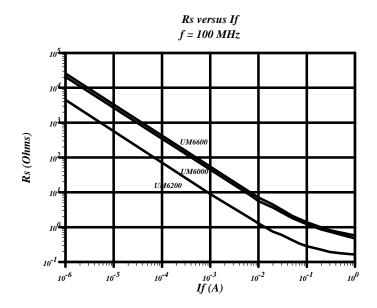




Style "B"

Style "SM"

## UM6000/UM6200/UM6600

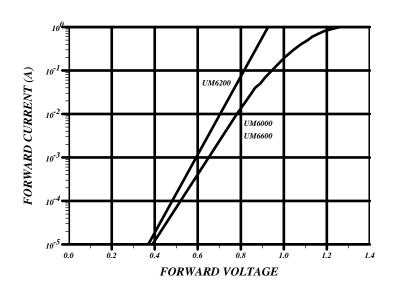




## **POWER PIN DIODES**

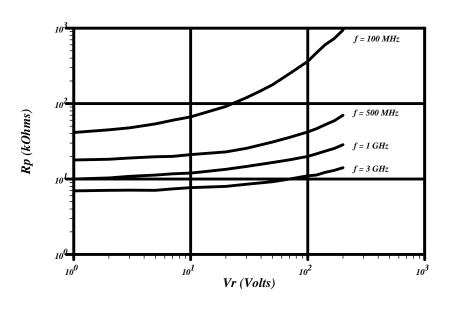
### UM6000/UM6200/UM6600

FORWARD VOLTAGE versus CURRENT



## UM6000/UM6600

### Rp versus Vr

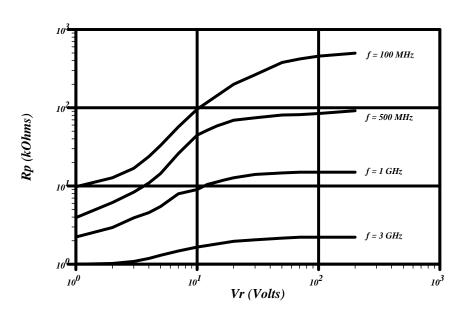




## **POWER PIN DIODES**

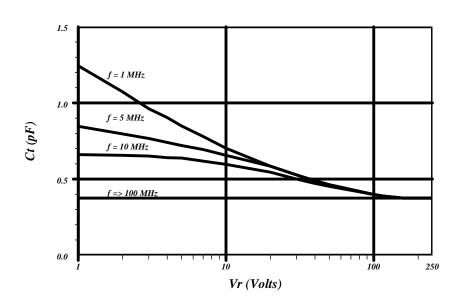
## **UM6200**

Rp versus Vr



## **UM6000**

#### Ct versus Vr

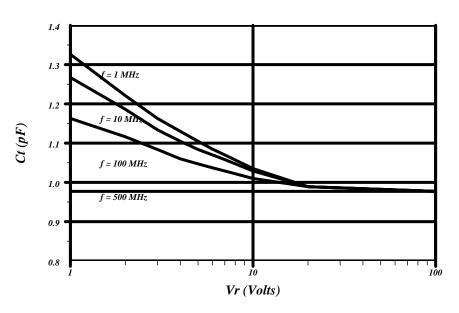




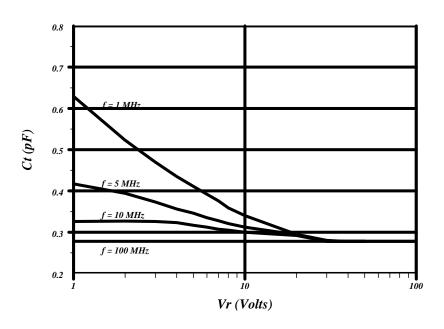
## **POWER PIN DIODES**

## **UM6200**

### Ct versus Vr



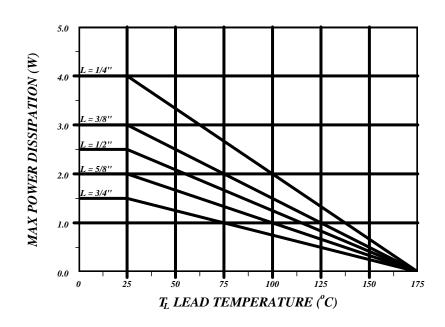
## UM6600 Ct versus Vr





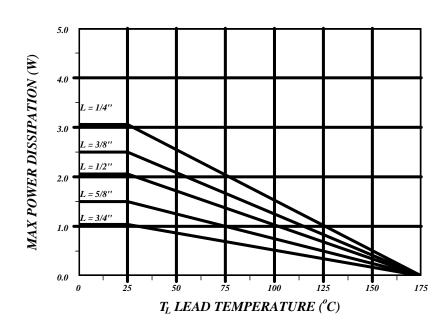
## **POWER PIN DIODES**

# UM6000/UM6200 MAX POWER DISSIPATION versus LEAD TEMPERATURE



UM6600

MAX POWER DISSIPATION versus LEAD TEMPERATURE

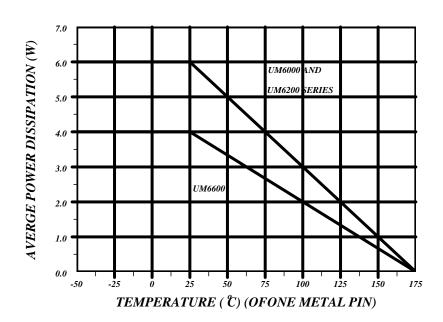




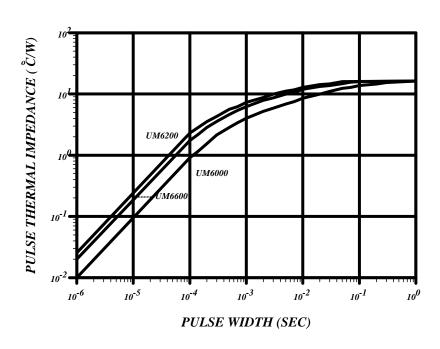
## **POWER PIN DIODES**

# UM6000/UM6200/UM6600

### **AVERGE POWER DISSIPATION versus TEMPERATURE**



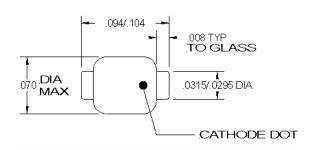
# UM6000/UM6200/UM6600 PULSE THERMAL IMPEDANCE VS PULSE WIDTH





## **POWER PIN DIODES**

## STYLE "A"



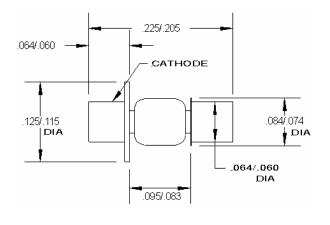
.019/.021 DIA

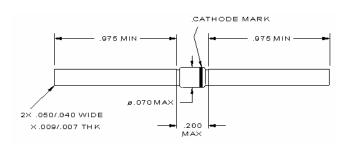
STYLE "E"

.070 DIA

STYLE "B"

## STYLE "C"

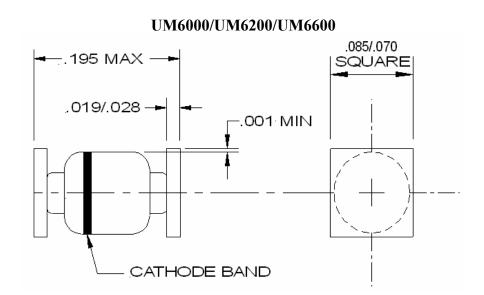




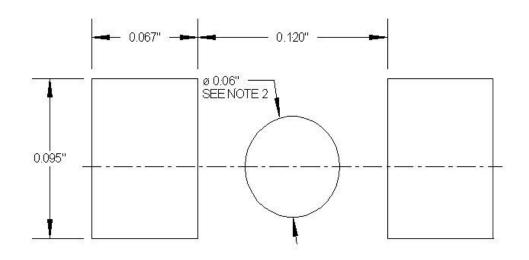
## STYLE "D" ø.125 x.060 THK BeO CERAMIC .600 MN TYP CATHODE Cu RIBBON (2 PL) .121/.128 WIDE X .005/.008 THK .210/.245 .119/.111 .190/.180 .035 MAX TO FIRST FULL .187 HEX **THREAD** 4-40 UNC-2A



## **POWER PIN DIODES**



## UM6000/UM6200/UM6600 STYLE "SM" FOOTPRINT





## **POWER PIN DIODES**

## NOTES:

- 1. These dimensions will match the terminals and provide for additional solder fillets at the outboard ends at least as wide as the terminals themselves, assuming accuracy of placement within 0.005"
- 2. If the mounting method chosen requires use of an adhesive separate from the solder compound, a round (or square) spot of cement as shown should be centrally located.

**NOTES:**